

Notice of References Cited		Application/Control Number 09/523,491	Applicant(s)/Patent Under Reexamination KLAUS ET AL.	
		Examiner Eric B Fuller	Art Unit 1762	Page 1 of 1

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	C	US-5,175,017	12-1992	Kobayashi et al.	427/8
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.